## TOSHIBA Transistor Silicon PNP / NPN Epitaxial Type (PCT Process)

## HN4B101J

## MOS Gate Drive Applications

## Switching Applications

- Small footprint due to a small and thin package
- High DC current gain : hFE $=200$ to 500 ( $\mathrm{IC}=-0.12 \mathrm{~A}$ )
- Low collector-emitter saturation: PNP $\mathrm{V}_{\mathrm{CE}}$ (sat) $=-0.20 \mathrm{~V}$ (max)

$$
: \mathrm{NPN} \quad \mathrm{~V}_{\mathrm{CE}}(\text { sat })=0.17 \mathrm{~V} \text { (max) }
$$

- High-speed switching : PNP $\mathrm{t}_{\mathrm{f}}=45 \mathrm{~ns}$ (typ.)

$$
\text { : NPN } \quad \mathrm{tf}_{\mathrm{f}}=50 \mathrm{~ns} \text { (typ.) }
$$

## Absolute Maximum Ratings ( $\mathrm{Ta}=\mathbf{2 5}{ }^{\circ} \mathrm{C}$ )

| Characteristic |  | Symbol | Rating |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
|  |  | PNP | NPN |  |
| Collector-base voltage |  |  | $\mathrm{V}_{\text {CBO }}$ | -30 | 50 | V |
| Collector-emitter voltage |  | $\mathrm{V}_{\text {CEO }}$ | -30 | 30 | V |
| Emitter-base voltage |  | $\mathrm{V}_{\text {Ebo }}$ | -7 | 7 | V |
| Collector current | DC (Note 1) | Ic | -1.0 | 1.2 | A |
|  | Pulse (Note 1) | ICP | -5.0 | 5.0 |  |
| Base current |  | $\mathrm{I}_{\mathrm{B}}$ | -120 | 120 | mA |
| Collector power dissipation (t = 10 s) | Single-device operation | PC (Note 2) | 0.85 |  | W |
| Collector power dissipation (DC) | Single-device operation | PC (Note 2) | 0.55 |  | W |
| Junction temperature |  | $\mathrm{T}_{\mathrm{j}}$ | 150 |  | ${ }^{\circ} \mathrm{C}$ |
| Storage temperature range |  | $\mathrm{T}_{\text {stg }}$ | -55 to 150 |  | ${ }^{\circ} \mathrm{C}$ |

Note 1: Ensure that the channel temperature does not exceed $150^{\circ} \mathrm{C}$ during use of the device.
Note 2: Mounted on an FR4 board (glass-epoxy; 1.6 mm thick; Cu area, $645 \mathrm{~mm}^{2}$ )
Note 3: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Figure 1. Circuit Configuration (top view)
Figure 2. Marking


Electrical Characteristics ( $\mathrm{Ta}=\mathbf{2 5}{ }^{\circ} \mathrm{C}$ )
PNP

| Characteristic |  | Symbol | Test Condition | Min | Typ. | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Collector cut-off current |  | ICBO | $\mathrm{V}_{\mathrm{CB}}=-30 \mathrm{~V}, \mathrm{I}_{\mathrm{E}}=0$ | - | - | -100 | nA |
| Emitter cut-off current |  | IEBO | $\mathrm{V}_{\mathrm{EB}}=-7 \mathrm{~V}, \mathrm{I}=0$ | - | - | -100 | nA |
| Collector-emitter breakdown voltage |  | $V$ (BR) CEO | $\mathrm{I}_{\mathrm{C}}=-10 \mathrm{~mA}, \mathrm{I}_{\mathrm{B}}=0$ | -30 | - | - | V |
| DC current gain |  | $\mathrm{h}_{\text {FE }}$ (1) | $\mathrm{V}_{\mathrm{CE}}=-2 \mathrm{~V}, \mathrm{I}_{\mathrm{C}}=-0.12 \mathrm{~A}$ | 200 | - | 500 |  |
|  |  | $\mathrm{h}_{\text {FE }}$ (2) | $\mathrm{V}_{\mathrm{CE}}=-2 \mathrm{~V}, \mathrm{I}_{\mathrm{C}}=-0.4 \mathrm{~A}$ | 125 | - | - |  |
| Collector-emitter saturation voltage |  | $\mathrm{V}_{\text {CE (sat) }}$ | $\mathrm{I}_{\mathrm{C}}=-0.4 \mathrm{~A}, \mathrm{I}_{\mathrm{B}}=-13 \mathrm{~mA}$ | - | - | -0.20 | V |
| Base-emitter saturation voltage |  | $V_{\text {BE (sat) }}$ | $\mathrm{I}_{\mathrm{C}}=-0.4 \mathrm{~A}, \mathrm{I}_{\mathrm{B}}=-13 \mathrm{~mA}$ | - | - | -1.10 | V |
| Collector output capacitance |  | $\mathrm{C}_{\text {ob }}$ | $\mathrm{V}_{\mathrm{CB}}=-10 \mathrm{~V}, \mathrm{I}_{\mathrm{E}}=0, \mathrm{f}=1 \mathrm{MHz}$ | - | 7.8 | - | pF |
| Switching time | Rise time | $t_{r}$ | See Figure 3 circuit diagram <br> $V_{C C} \simeq-16 \mathrm{~V}, R_{L}=40 \Omega$ <br> $\mathrm{I}_{\mathrm{B} 1}=\mathrm{I}_{\mathrm{B} 2}=13 \mathrm{~mA}$ | - | 40 | - | ns |
|  | Storage time | $\mathrm{t}_{\text {stg }}$ |  | - | 200 | - |  |
|  | Fall time | $t_{f}$ |  | - | 45 | - |  |

NPN

| Characteristic |  | Symbol | Test Condition | Min | Typ. | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Collector cut-off current |  | ICBO | $\mathrm{V}_{\mathrm{CB}}=50 \mathrm{~V}, \mathrm{I}_{\mathrm{E}}=0$ | - | - | 100 | nA |
| Emitter cut-off current |  | IEBO | $\mathrm{V}_{\mathrm{EB}}=7 \mathrm{~V}, \mathrm{I}_{\mathrm{C}}=0$ | - | - | 100 | nA |
| Collector-emitter breakdown voltage |  | $V$ (BR) CEO | $\mathrm{I}_{\mathrm{C}}=10 \mathrm{~mA}, \mathrm{I}_{\mathrm{B}}=0$ | 30 | - | - | V |
| DC current gain |  | $h_{\text {FE }}$ (1) | $\mathrm{V}_{\mathrm{CE}}=2 \mathrm{~V}, \mathrm{I}_{\mathrm{C}}=0.12 \mathrm{~A}$ | 200 | - | 500 |  |
|  |  | $\mathrm{h}_{\text {FE }}$ (2) | $\mathrm{V}_{\mathrm{CE}}=2 \mathrm{~V}, \mathrm{I}_{\mathrm{C}}=0.4 \mathrm{~A}$ | 125 | - | - |  |
| Collector-emitter saturation voltage |  | $\mathrm{V}_{\text {CE (sat) }}$ | $\mathrm{I}_{\mathrm{C}}=0.4 \mathrm{~A}, \mathrm{I}_{\mathrm{B}}=13 \mathrm{~mA}$ | - | - | 0.17 | V |
| Base-emitter saturation voltage |  | $V_{B E}$ (sat) | $\mathrm{I}_{\mathrm{C}}=0.4 \mathrm{~A}, \mathrm{I}_{\mathrm{B}}=13 \mathrm{~mA}$ | - | - | 1.10 | V |
| Collector output capacitance |  | $\mathrm{C}_{\mathrm{ob}}$ | $\mathrm{V}_{\mathrm{CB}}=10 \mathrm{~V}, \mathrm{I}_{\mathrm{E}}=0, \mathrm{f}=1 \mathrm{MHz}$ | - | 7.0 | - | pF |
| Switching time | Rise time | $\mathrm{tr}_{r}$ | See Figure 4 circuit diagram $\mathrm{V}_{\mathrm{CC}} \simeq 16 \mathrm{~V}, \mathrm{R}_{\mathrm{L}}=40 \Omega$ <br> $\mathrm{I}_{\mathrm{B} 1}=-\mathrm{I}_{\mathrm{B} 2}=13 \mathrm{~mA}$ | - | 45 | - | ns |
|  | Storage time | $\mathrm{t}_{\text {stg }}$ |  | - | 450 | - |  |
|  | Fall time | $t_{f}$ |  | - | 50 | - |  |

Figure 3. Switching Time Test Circuit \& Timing Chart


PNP







## NPN







Safe operating area


## Common



Permissible Power Dissipation for Simultaneous Operation



Collector power dissipation at single-device operation is
0.55 W .

Collector power dissipation at single-device value at
dual operation is 0.31 W
Collector power dissipation at dual operation is set to 0.62 W.

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